

# **One Watt Amplifier Transistors NPN Silicon**

# MPSW05 MPSW06\*

\*On Semiconductor Preferred Device

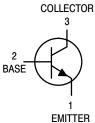
# **MAXIMUM RATINGS**

| Rating  | Symbol                            | MPSW05      | MPSW06 | Unit           |
|---|-----------------------------------|-------------|--------|----------------|
| Collector–Emitter Voltage   | V <sub>CEO</sub>                  | 60          | 80     | Vdc            |
| Collector-Base Voltage  | V <sub>CBO</sub>                  | 60          | 80     | Vdc            |
| Emitter-Base Voltage  | V <sub>EBO</sub>                  | 4.0         |        | Vdc            |
| Collector Current — Continuous  | I <sub>C</sub>                    | 500         |        | mAdc           |
| Total Device Dissipation @ T <sub>A</sub> = 25°C<br>Derate above 25°C | P <sub>D</sub>                    | 1.0<br>8.0  |        | Watt<br>mW/°C  |
| Total Device Dissipation @ T <sub>C</sub> = 25°C<br>Derate above 25°C | P <sub>D</sub>                    | 2.5<br>20   |        | Watts<br>mW/°C |
| Operating and Storage Junction<br>Temperature Range                   | T <sub>J</sub> , T <sub>stg</sub> | -55 to +150 |        | °C             |



# THERMAL CHARACTERISTICS

| Characteristic                          | Symbol          | Max | Unit |
|---|-----------------|-----|------|
| Thermal Resistance, Junction to Ambient | $R_{\theta JA}$ | 125 | °C/W |
| Thermal Resistance, Junction to Case    | $R_{\theta JC}$ | 50  | °C/W |



# **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

| Characteristic   |                  | Symbol               | Min      | Max        | Unit |
|--|------------------|----------------------|----------|------------|------|
| OFF CHARACTERISTICS  |                  |                      |          |            |      |
| Collector–Emitter Breakdown Voltage <sup>(1)</sup> (I <sub>C</sub> = 1.0 mAdc, I <sub>B</sub> = 0) | MPSW05<br>MPSW06 | V <sub>(BR)CEO</sub> | 60<br>80 | _          | Vdc  |
| Emitter–Base Breakdown Voltage ( $I_E = 100 \mu Adc$ , $I_C = 0$ )                                 |                  | V <sub>(BR)EBO</sub> | 4.0      | _          | Vdc  |
| Collector Cutoff Current $(V_{CE} = 40 \text{ Vdc}, I_B = 0)$ $(V_{CE} = 60 \text{ Vdc}, I_B = 0)$ | MPSW05<br>MPSW06 | I <sub>CES</sub>     | _        | 0.5<br>0.5 | μAdc |
| Collector Cutoff Current $(V_{CB} = 40 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 60 \text{ Vdc}, I_E = 0)$ | MPSW05<br>MPSW06 | I <sub>CBO</sub>     |          | 0.1<br>0.1 | μAdc |
| Emitter Cutoff Current (V <sub>EB</sub> = 3.0 Vdc, I <sub>C</sub> = 0)                             |                  | I <sub>EBO</sub>     | _        | 0.1        | μAdc |

<sup>1.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%.

Preferred devices are ON Semiconductor recommended choices for future use and best overall value.

# MPSW05 MPSW06

# **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted) (Continued)

| Characteristic   | Symbol               | Min      | Max | Unit |
|--|----------------------|----------|-----|------|
| ON CHARACTERISTICS <sup>(1)</sup>  | •                    | •        | •   | •    |
| DC Current Gain ( $I_C = 50 \text{ mAdc}$ , $V_{CE} = 1.0 \text{ Vdc}$ ) ( $I_C = 250 \text{ mAdc}$ , $V_{CE} = 1.0 \text{ Vdc}$ ) | h <sub>FE</sub>      | 80<br>60 |     | _    |
| Collector–Emitter Saturation Voltage (I <sub>C</sub> = 250 mAdc, I <sub>B</sub> = 10 mAdc)   | V <sub>CE(sat)</sub> | _        | 0.4 | Vdc  |
| Base–Emitter Saturation Voltage ( $I_C = 250 \text{ mAdc}$ , $V_{CE} = 5.0 \text{ Vdc}$ )  | V <sub>BE(sat)</sub> | _        | 1.2 | Vdc  |
| SMALL-SIGNAL CHARACTERISTICS   |                      | •        | •   | •    |
| Current–Gain — Bandwidth Product ( $I_C = 200 \text{ mAdc}$ , $V_{CE} = 5.0 \text{ Vdc}$ , $f = 20 \text{ MHz}$ )                  | f <sub>T</sub>       | 50       | _   | MHz  |
| Output Capacitance<br>(V <sub>CB</sub> = 10 V, f = 1.0 MHz)  | C <sub>obo</sub>     | _        | 12  | pF   |

<sup>1.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%.

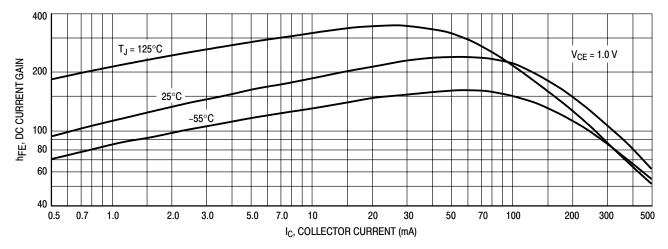


Figure 1. DC Current Gain

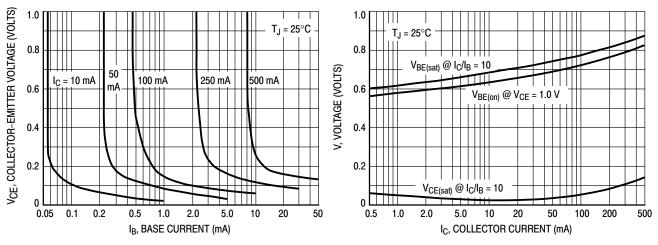


Figure 2. Collector Saturation Region

Figure 3. "On" Voltages

# MPSW05 MPSW06

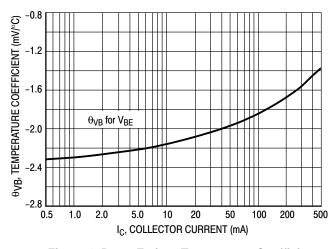


Figure 4. Base–Emitter Temperature Coefficient

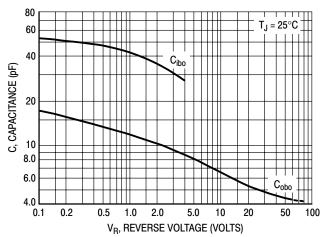


Figure 5. Capacitance

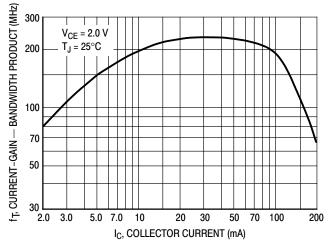


Figure 6. Current-Gain — Bandwidth Product

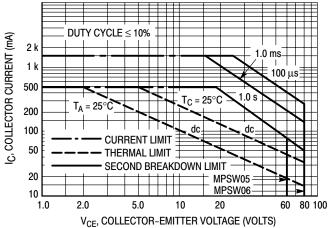
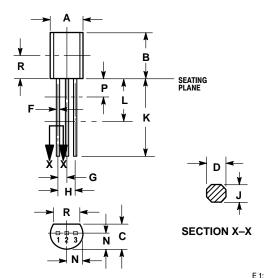


Figure 7. Active Region — Safe Operating Area

### MPSW05 MPSW06

# PACKAGE DIMENSIONS

TO-92 (TO-226) **CASE 29-10 ISSUE AL** 



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.
  3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.

  . DIMENSION F APPLIES BETWEEN P AND L.
- DIMENSIONS D AND J APPLY BETWEEN L AND K
  MIMIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

|     | INCHES |       | MILLIMETERS |       |
|-----|--------|-------|-------------|-------|
| DIM | MIN    | MAX   | MIN         | MAX   |
| Α   | 0.175  | 0.205 | 4.44        | 5.21  |
| В   | 0.290  | 0.310 | 7.37        | 7.87  |
| С   | 0.125  | 0.165 | 3.18        | 4.19  |
| D   | 0.018  | 0.021 | 0.457       | 0.533 |
| F   | 0.016  | 0.019 | 0.407       | 0.482 |
| G   | 0.045  | 0.055 | 1.15        | 1.39  |
| Н   | 0.095  | 0.105 | 2.42        | 2.66  |
| J   | 0.018  | 0.024 | 0.46        | 0.61  |
| K   | 0.500  |       | 12.70       |       |
| L   | 0.250  |       | 6.35        |       |
| N   | 0.080  | 0.105 | 2.04        | 2.66  |
| Р   |        | 0.100 |             | 2.54  |
| R   | 0.135  |       | 3.43        |       |

PIN 1 FMITTER BASE COLLECTOR

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